30V N-Channel NexFET™ Power MOSFET

Check for Samples: CSD17303Q5

FEATURES

- **Optimized for 5V Gate Drive**
- **Ultralow Q_g and Q_{gd}**
- **Low Thermal Resistance**
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- **SON 5-mm × 6-mm Plastic Package**

APPLICATIONS

- **Notebook Point-of-Load**
- **Point-of-Load Synchronous Buck in Networking, Telecom and Computing Systems**
- **Optimized for Synchronous FET Applications**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications, and optimized for 5V gate drive applications.

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	30		V
Q_g	Gate Charge Total (4.5V)	18		nC
Q_{gd}	Gate Charge Gate to Drain	4		nC
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 3V	2.7	mΩ
		V_{GS} = 4.5V	2	mΩ
		V_{GS} = 8V	1.7	mΩ
$V_{GS(th)}$	Threshold Voltage	1.1		V

ORDERING INFORMATION

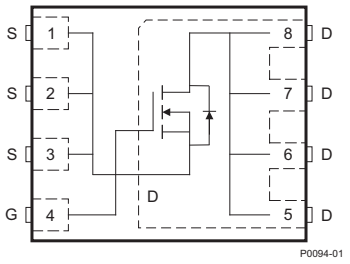
Device	Package	Media	Qty	Ship
CSD17303Q5	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

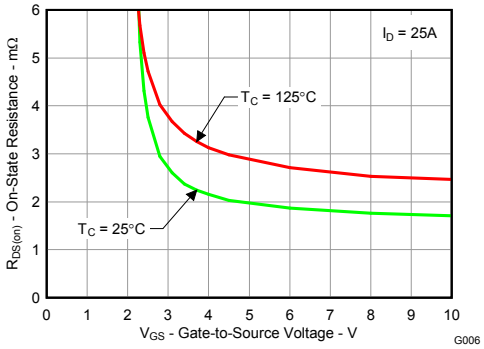
T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	+10 / –8	V
I_D	Continuous Drain Current, T_C = 25°C	100	A
	Continuous Drain Current(1)	32	A
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	200	A
P_D	Power Dissipation(1)	3.2	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse I_D = 103A, L = 0.1mH, R_G = 25Ω	530	mJ

(1) $R_{\theta JA}$ = 39°C/W on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
(2) Pulse duration ≤300μs, duty cycle ≤2%"

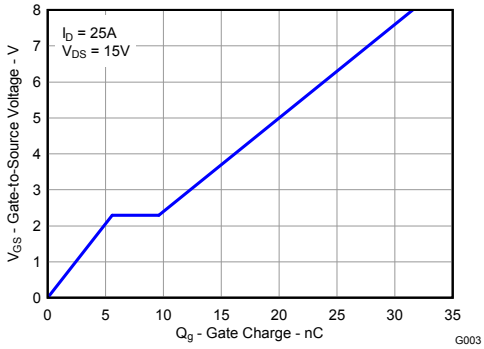
Top View



$R_{DS(on)}$ vs V_{GS}



GATE CHARGE



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ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

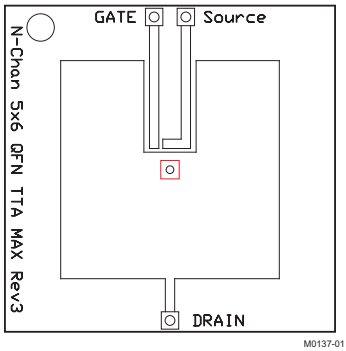
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = 250µA	30			V
I_{DSS}	Drain to Source Leakage Current	V_{GS} = 0V, V_{DS} = 24V			1	µA
I_{GSS}	Gate to Source Leakage Current	V_{DS} = 0V, V_{GS} = +10/–8V			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	0.9	1.1	1.6	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 3V, I_D = 25A		2.7	3.7	mΩ
		V_{GS} = 4.5V, I_D = 25A		2	2.6	mΩ
		V_{GS} = 8V, I_D = 25A		1.7	2.4	mΩ
g_{fs}	Transconductance	V_{DS} = 15V, I_D = 25A		114		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		2630	3420	pF
C_{oss}	Output Capacitance			1440	1870	pF
C_{rss}	Reverse Transfer Capacitance			83	108	pF
R_G	Series Gate Resistance			1.4	2.8	Ω
Q_g	Gate Charge Total (4.5V)	V_{DS} = 15V, I_{DS} = 25A		18	23	nC
Q_{gd}	Gate Charge Gate to Drain			4		nC
Q_{gs}	Gate Charge Gate to Source			5.6		nC
$Q_{g(th)}$	Gate Charge at Vth			3		nC
Q_{oss}	Output Charge	V_{DS} = 13.7V, V_{GS} = 0V		34		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 15V, V_{GS} = 4.5V, I_{DS} = 25A, R_G = 2Ω		11.4		ns
t_r	Rise Time			16		ns
$t_{d(off)}$	Turn Off Delay Time			27		ns
t_f	Fall Time			10.4		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_{SD} = 25A, V_{GS} = 0V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DD} = 13.7V, I_F = 25A, di/dt = 300A/µs		50		nC
t_{rr}	Reverse Recovery Time			33		ns

THERMAL CHARACTERISTICS

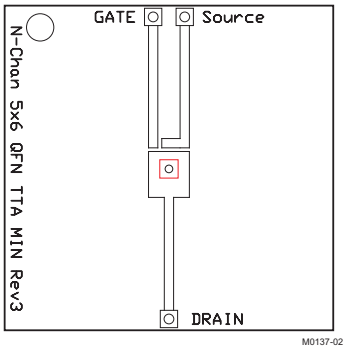
(T_A = 25°C unless otherwise stated)

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1)			1.1	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1)(2)			49	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 49°C/W when mounted on 1 inch^2 (6.45 cm^2) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 124°C/W when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

T_A = 25°C, unless otherwise specified

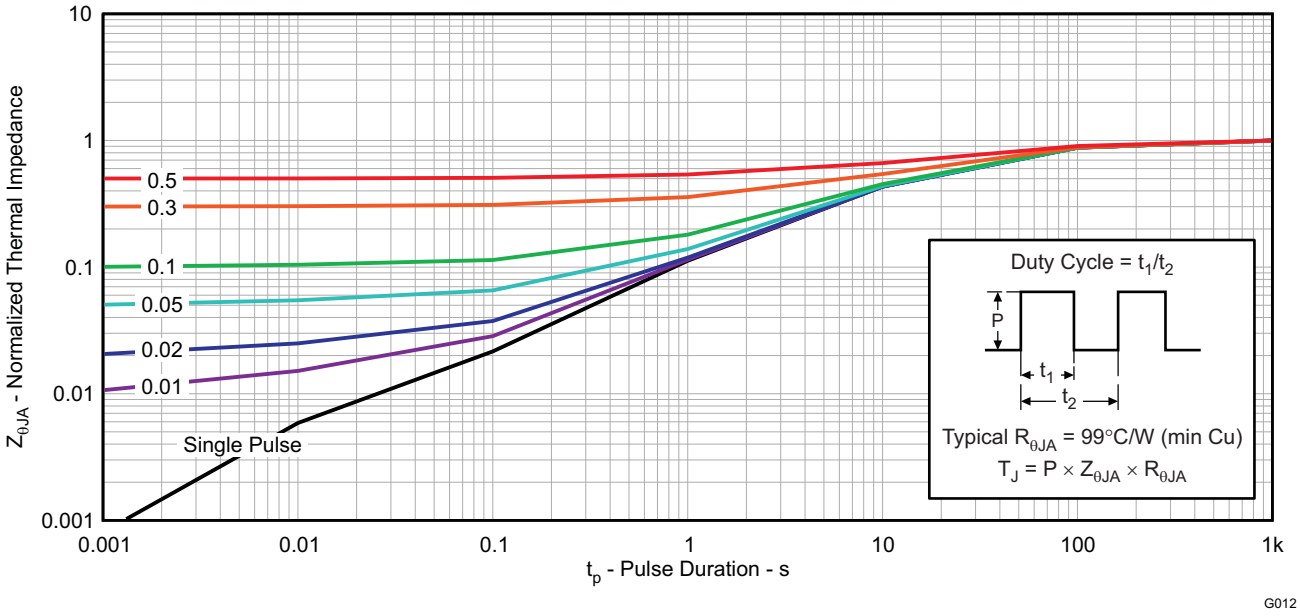


Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

T_A = 25°C, unless otherwise specified

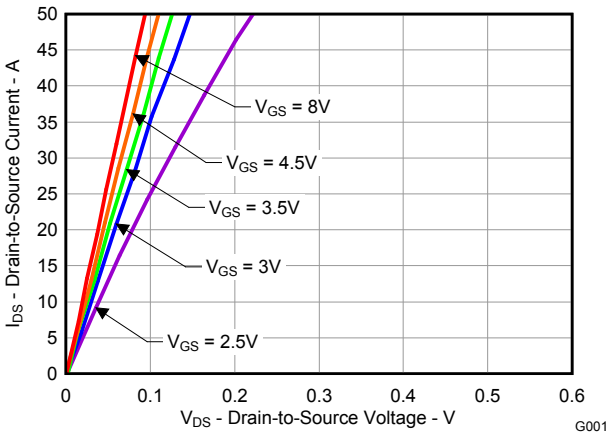


Figure 2. Saturation Characteristics

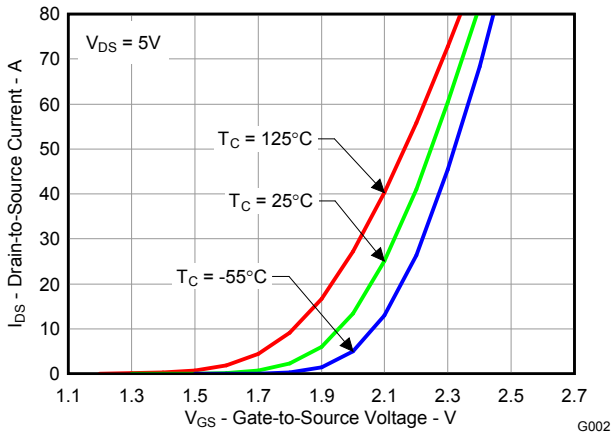


Figure 3. Transfer Characteristics

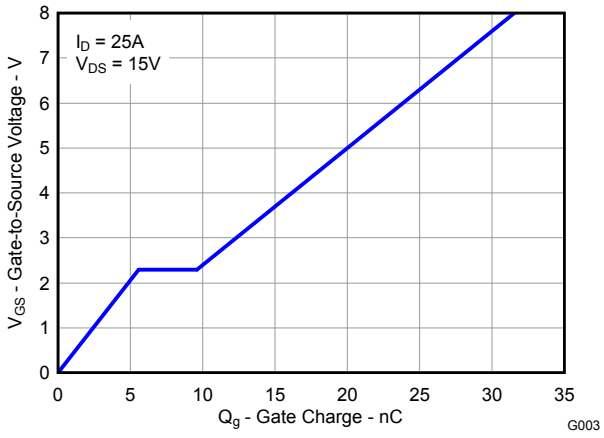


Figure 4. Gate Charge

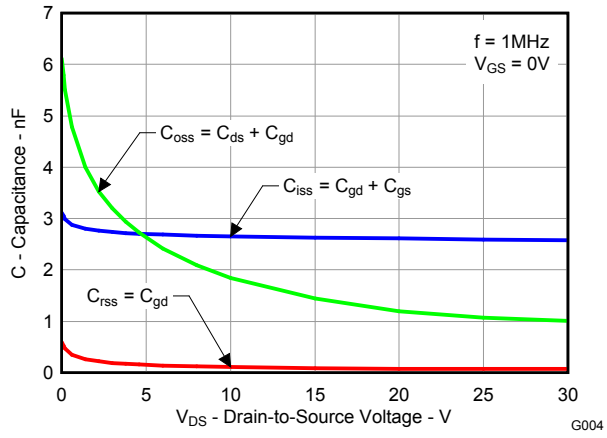


Figure 5. Capacitance

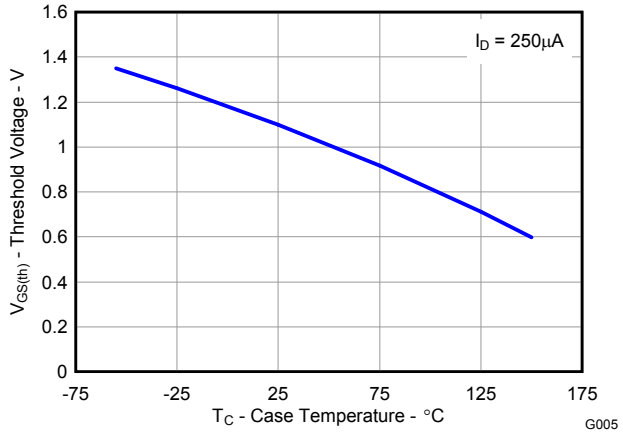


Figure 6. Threshold Voltage vs. Temperature

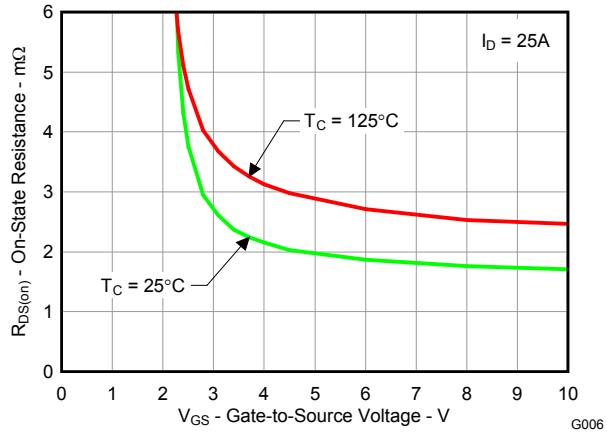


Figure 7. On-State Resistance vs. Gate-to-Source Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

T_A = 25°C, unless otherwise specified

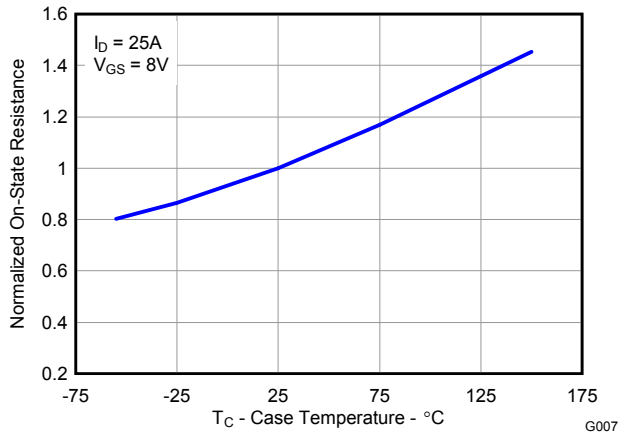


Figure 8. Normalized On-State Resistance vs. Temperature

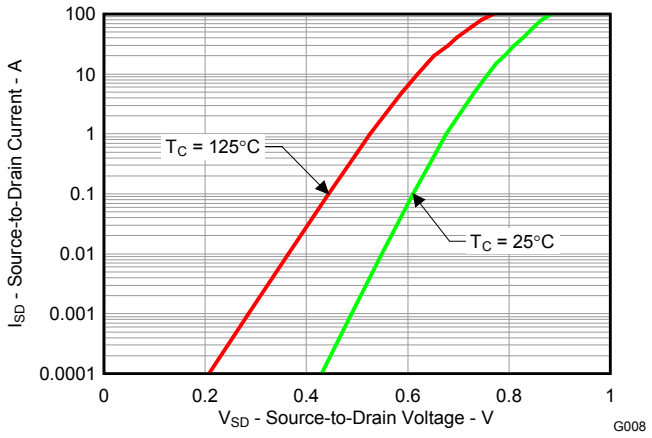


Figure 9. Typical Diode Forward Voltage

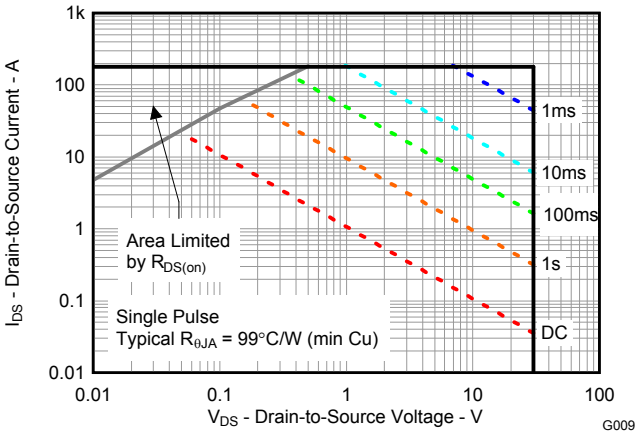


Figure 10. Maximum Safe Operating Area

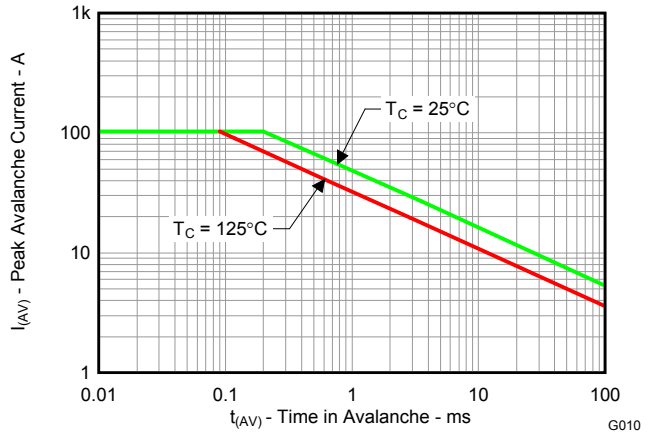


Figure 11. Single Pulse Unclamped Inductive Switching

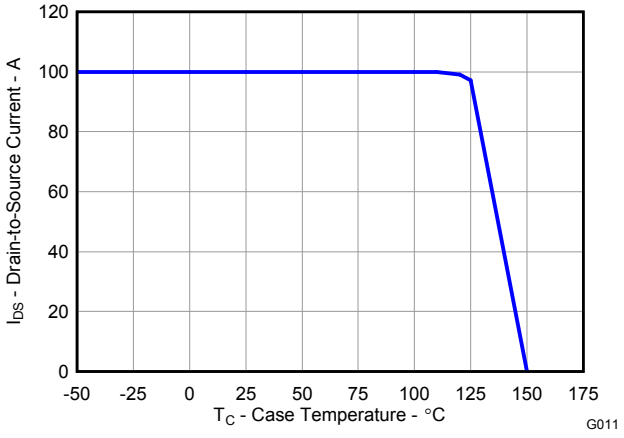
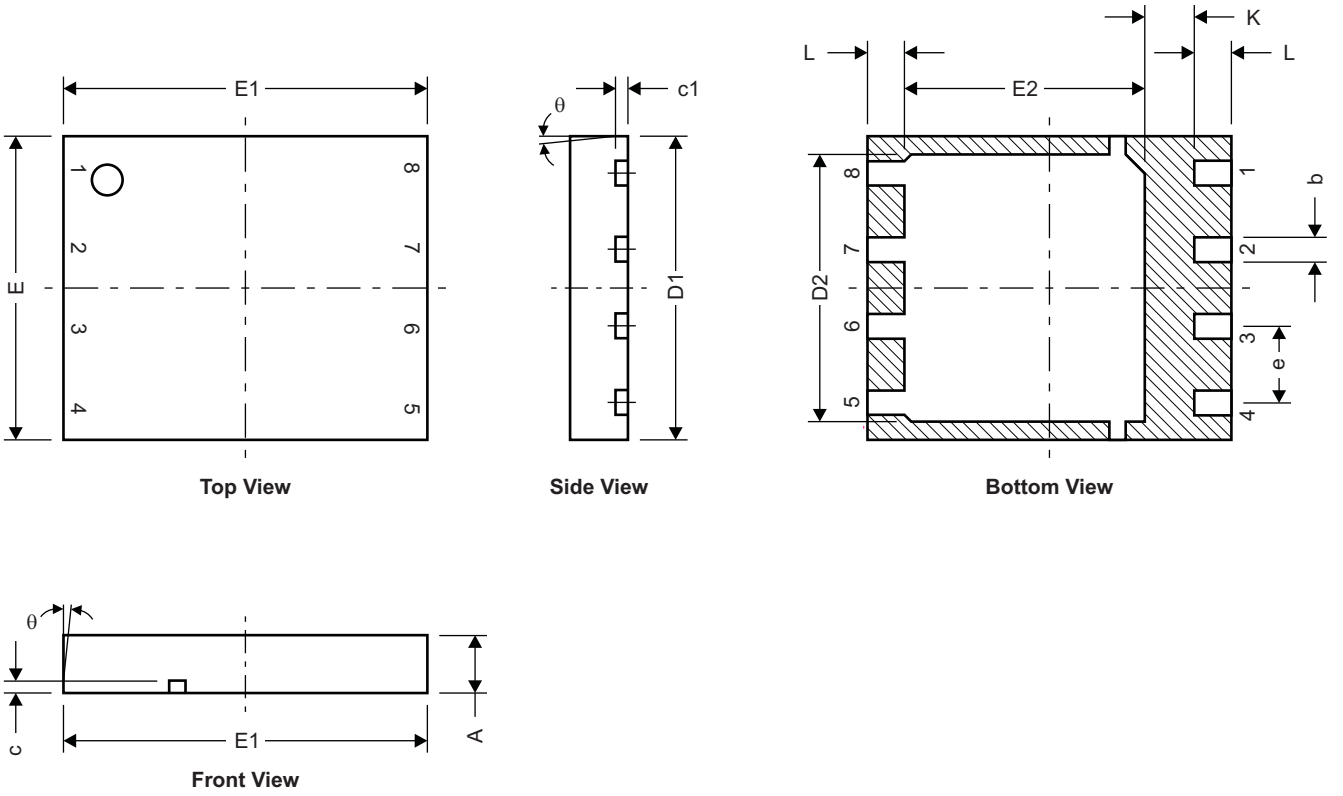


Figure 12. Maximum Drain Current vs. Temperature

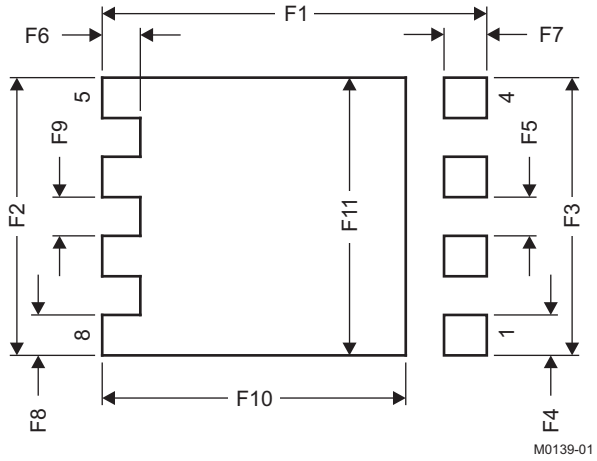
MECHANICAL DATA

Q5 Package Dimensions



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
K	0.760		0.030	
L	0.510	0.710	0.020	0.028
θ	0.00			

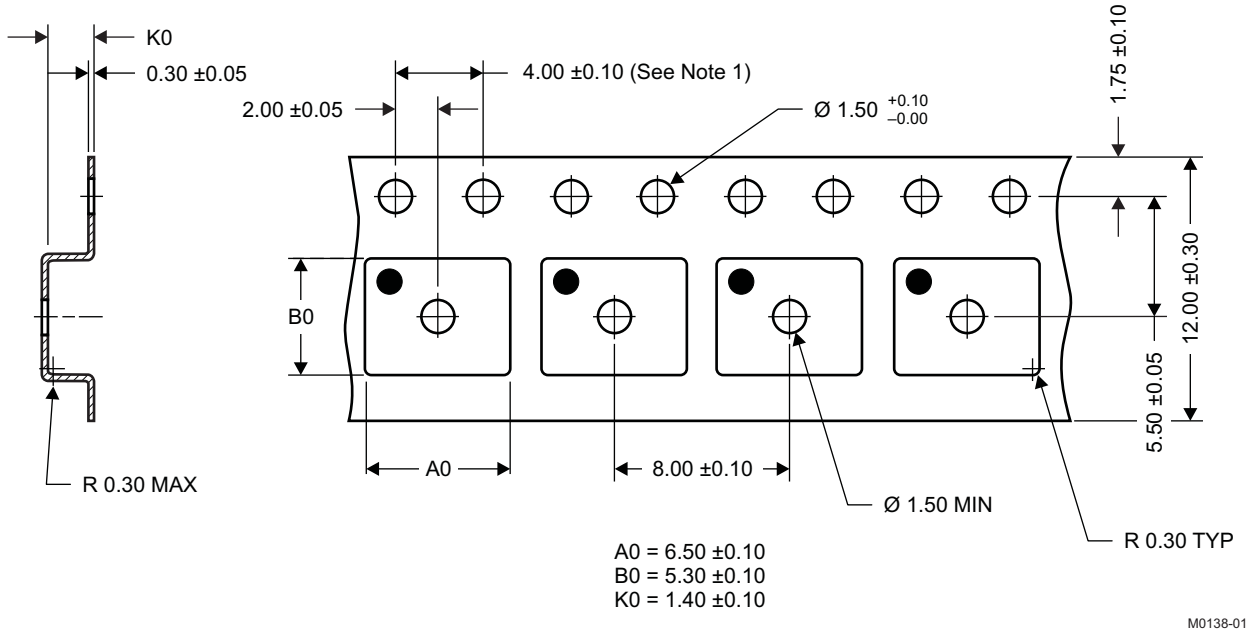
Recommended PCB Pattern



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

Q5 Tape and Reel Information



Notes:

1. 10-sprocket hole-pitch cumulative tolerance ±0.2
2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified)
5. Thickness: 0.30 ±0.05mm
6. MSL1 260°C (IR and convection) PbF reflow compatible

Package Marking Information

Location

1st Line

CSD = Fixed Characters

NNNNN = Product Code

2nd Line (Date Code)

YY = Last 2 digits of the Year

WW = 2-digit Work Week

C = Country of Origin

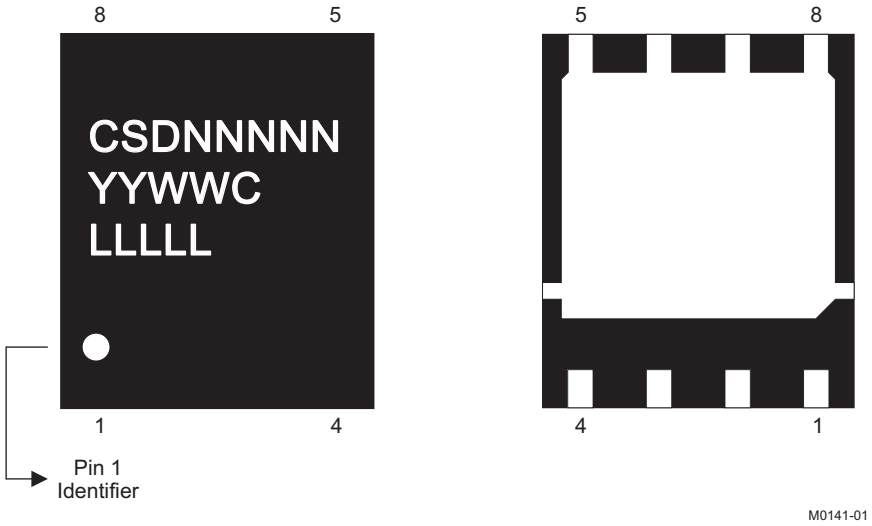
> Philippines = P

> Taiwan = T

> China = C

3rd Line

LLLL = Last 5 digits of the Wafer Lot #



REVISION HISTORY

Changes from Original (January 2010) to Revision A **Page**

- Changed the Abs Max Ratings table, Avalanche Energy, single pulse From: I_D = 85A, L = 0.1mH, R_G = 25Ω Value = 361 To: I_D = 103A, L = 0.1mH, R_G = 25Ω Value = 530 1
- Changed Figure 11 5

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